80 V NPN, 10 A Power Transistor

These series of plastic, silicon NPN power transistors can be used as general purpose power amplification and switching such as output or driver stages in applications such as switching regulators, converters and power amplifiers.

Features

- Fast Switching Speeds
- High Frequency
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Benefits

- Reliable Performance at Higher Powers
- Symmetrical Characteristics in Complementary Configurations
- Accurate Reproduction of Input Signal
- Greater Dynamic Range
- High Amplifier Bandwidth

Applications

- High-end Consumer Audio Products
 - Home Amplifiers
 - Home Receivers

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	80	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current - Continuous	Ic	10	Α
Collector Current - Peak (Note 1)	I _{CM}	20	Α
Total Power Dissipation @ T _C = 25°C	P_{D}	120	Watts

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	1.04	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle \leq 10%.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

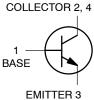


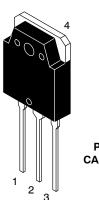
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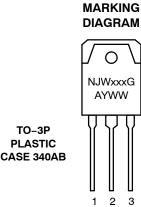
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80 VOLT, 10 AMPS NPN POWER TRANSISTORS

NPN







3 I 1

xxx = TBD

G = Pb-Free Package
A = Assembly Location

YearWork Week

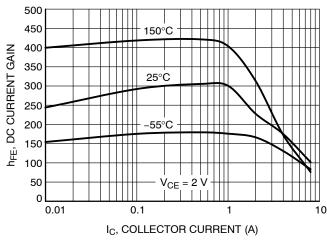
ORDERING INFORMATION

Device	Package	Shipping
NJW44H11G	TO-3P (Pb-Free)	30 Units/Rail

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•		
Collector–Emitter Sustaining Voltage ($I_C = 30 \text{ mAdc}, I_B = 0$)	V _{CEO}	80	_	_	Vdc
Collector–Cutoff Current $(V_{CE} = Rated V_{CEO}, V_{BE} = 0)$	I _{CES}	-	-	10	μAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc)	I _{EBO}	-	_	10	μAdc
ON CHARACTERISTICS			•	•	•
DC Current Gain $ (I_C = 2 \text{ A, } V_{CE} = 2 \text{ V}) $ $ (I_C = 4 \text{ A, } V_{CE} = 2 \text{ V}) $	h _{FE}	100 80	- -	400 320	-
Collector-Emitter Saturation Voltage (I _C = 8 A, I _B = 400 mA)	V _{CE(sat)}	-	-	1.0	V
Base-Emitter Turn-on Voltage (I _C = 8 A, V _{CE} = 2.0 V)	V _{BE(on)}	-	-	1.5	V
DYNAMIC CHARACTERISTICS	<u>-</u>		-		=
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)	C _{obo}	-	65	-	pF
Cutoff Frequency ($I_C = 500 \text{ mA}$, $V_{CE} = 5 \text{ V}$, $f = 1.0 \text{ MHz}$)	f⊤	-	85	-	MHz
SWITCHING TIMES	<u>.</u>	•	•	•	•
Delay and Rise Times (I _C = 5.0 Adc, I _{B1} = 0.5 A)	$t_d + t_r$	-	300	-	ns
Storage Time $(I_C = 5.0 \text{ Adc}, I_{B1} = I_{B2} = 0.5 \text{ A})$	t _s	-	500	-	ns
Fall Time $(I_C = 5.0 \text{ Adc}, I_{B1} = I_{B2} = 0.5 \text{ A})$	t _f	-	140	-	ns

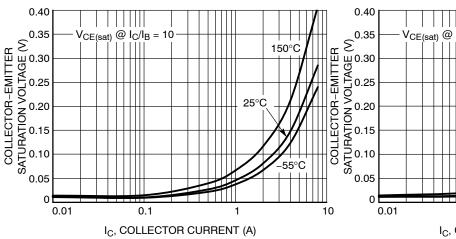
TYPICAL CHARACTERISTICS



500 450 150°C 400 hFE, DC CURRENT GAIN 350 25°C 300 250 200 -55°C 150 100 50 0 0.01 10 IC, COLLECTOR CURRENT (A)

Figure 1. DC Current Gain

Figure 2. DC Current Gain



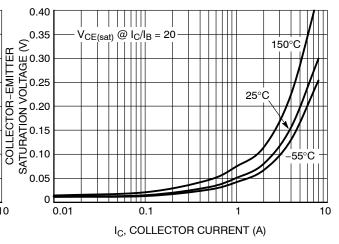
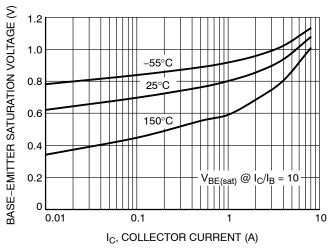


Figure 3. Collector Emitter Saturation Voltage

Figure 4. Collector Emitter Saturation Voltage



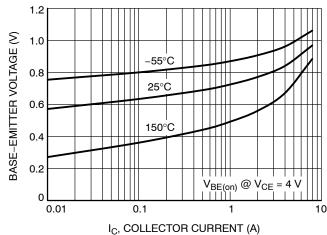
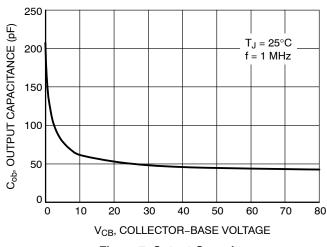


Figure 5. Base Emitter Saturation Voltage

Figure 6. Base Emitter "ON" Voltage

TYPICAL CHARACTERISTICS



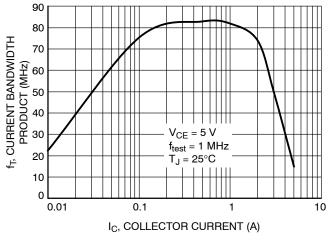
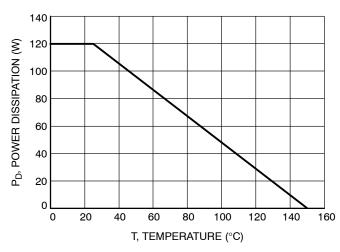


Figure 7. Output Capacitance

Figure 8. Current Gain Bandwidth Product





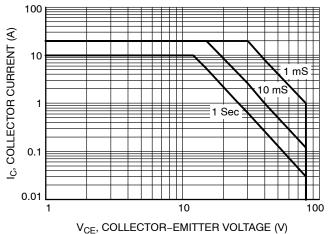
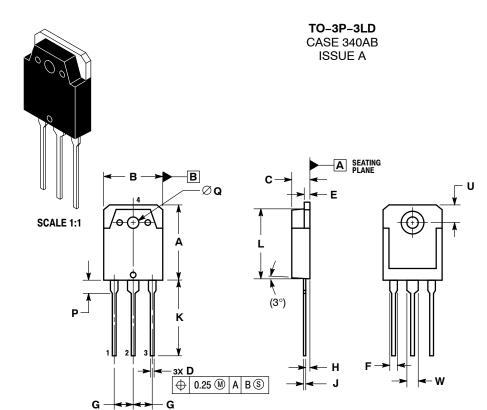


Figure 10. Safe Operating Area (SOA)

DATE 30 OCT 2007

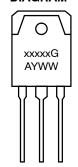




- IOIES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM THE TERMINAL TIP.
- DIMENSION A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	19.70	19.90	20.10	
В	15.40	15.60	15.80	
C	4.60	4.80	5.00	
D	0.80	1.00	1.20	
E	1.45	1.50	1.65	
F	1.80	2.00	2.20	
G	5.45 BSC			
Н	1.20	1.40	1.60	
J	0.55	0.60	0.75	
K	19.80	20.00	20.20	
L	18.50	18.70	18.90	
P	3.30	3.50	3.70	
Q	3.10	3.20	3.50	
U	5.00 REF			
W	2.80	3.00	3.20	

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Pb-Free Package G Α = Assembly Location

Υ = Year WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

2. COLLECTOR EMITTER COLLECTOR

PIN 1. BASE

STYLE 1:

STYLE 2: ANODE CATHODE 2. ANODE

CATHODE

STYLE 3: PIN 1. GATE

2. DRAIN SOURCE DRAIN

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